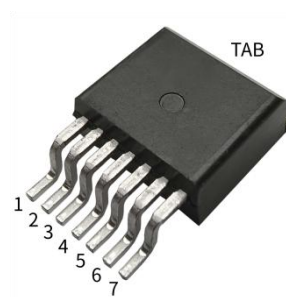
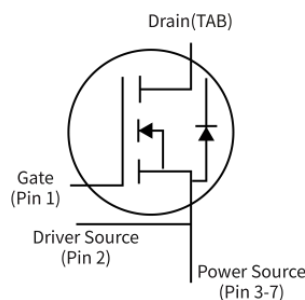


Silicon Carbide Power MOSFET

Parameter	Value	Unit
V_{DS}	3300	V
I_D	4	A
$R_{DS(ON)}$	1.0	Ω
Q_G	33	nC



TO-263-7L

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Avalanche Ruggedness
- Easy to Parallel and Simple to Drive

Applications

- Motor Drive
- Solar Inverters
- Battery Chargers
- High Voltage DC/DC Converters
- Switched-Mode Power Supply(SMPS)

Absolute Maximum Ratings (at $T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source Voltage	V_{DS}	3300	V
Gate-source Voltage (Absolute maximum values)	V_{GS}	-10/+25	V
Gate-source Voltage (Recommended operational values)		-5/+20	
Drain Current (continuous; $T_c=25^\circ\text{C}$) $V_{GS}=20\text{V}$	I_D	4	A
Drain Current (continuous; $T_c=100^\circ\text{C}$) $V_{GS}=20\text{V}$		2.5	
Drain Current (pulsed)	I_{DM}	16	A
Power Dissipation ($T_c=25^\circ\text{C}$, $T_J=175^\circ\text{C}$)	P_D	105	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.43	$^\circ\text{C/W}$
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	55	

Electrical Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Static characteristics (at T _C =25°C unless otherwise specified)						
Drain-Source Breakdown Voltage	B _{VDS}	V _{GS} =0V; I _D =100uA	3300	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =3300V; V _{GS} =0V	-	2	100	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =20V; V _{DS} =0V	-	-	100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} ; I _D =0.5mA; T _J =25°C	2.0	2.7	4.0	V
Static Drain-Source on Resistance	R _{DS(on)}	V _{GS} =20V; I _D =2A; T _J =25°C	-	1.0	1.5	Ω
		V _{GS} =20V; I _D =2A; T _J =175°C	-	2.2	-	
Transconductance	G _{fs}	V _{GS} =20V; I _D =2A; T _J =25°C	-	0.75	-	S
		V _{GS} =20V; I _D =2A; T _J =175°C	-	0.79	-	
Dynamic characteristics (at T _C =25°C unless otherwise specified)						
Input Capacitance	C _{iss}	V _{DS} =1200V; f=1MHz; V _{GS} =0V T _J =25°C	-	313	-	pF
Output Capacitance	C _{oss}		-	15	-	
Reverse Transfer Capacitance	C _{rss}		-	5.6	-	
Coss Stored Energy	E _{oss}		-	13	-	uJ
Turn on Switching Energy	E _{on}	V _{DD} =1200V; V _{GS} =-5/20V; I _D =2A; R _G =2.5Ω	-	89	-	uJ
Turn off Switching Energy	E _{off}		-	30	-	
Total Gate Charge	Q _G	V _{DD} =1200V; V _{GS} =-5/20V; I _D =2A; T _J =25°C	-	33	-	nC
Gate-Source Charge	Q _{GS}		-	5.6	-	
Gate-Drain Charge	Q _{GD}		-	12	-	
Internal Gate Resistor	R _{Gint}	f=1MHz; V _{AC} =25mV	-	2.6	-	Ω
Turn-on Delay Time	t _{d(on)}	V _{DD} =1200V; V _{GS} =-5/20V; I _D =2A; R _G =2.5Ω	-	6	-	ns
Rise Time	t _r		-	15	-	
Turn-off Delay Time	t _{d(off)}		-	15	-	
Fall Time	t _f		-	96	-	

Reverse SiC Diode Characteristics(at $T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Units
			Min.	Typ.	Max.	
Diode Forward Voltage	V_{FSD}	$V_{GS}=-5V$; $I_F=1A$; $T_J=25^\circ\text{C}$	-	9.0	11	V
Continuous Diode Forward Current	I_S	$T_C=25^\circ\text{C}$	-	4	-	A
Reverse Recovery Time	t_{RR}	$V_R=1200V$; $V_{GS}=0V$; $I_F=2A$; $di/dt=1000A/\mu s$	-	7.0	-	ns
Reverse Recovery Charge	Q_{RR}		-	26	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	6.3	-	A

Typical Characteristics

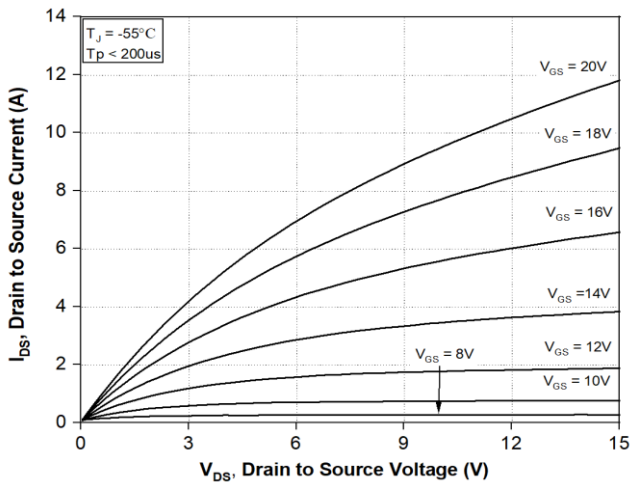


Figure 1. Output Characteristics $T_J = -55^\circ\text{C}$

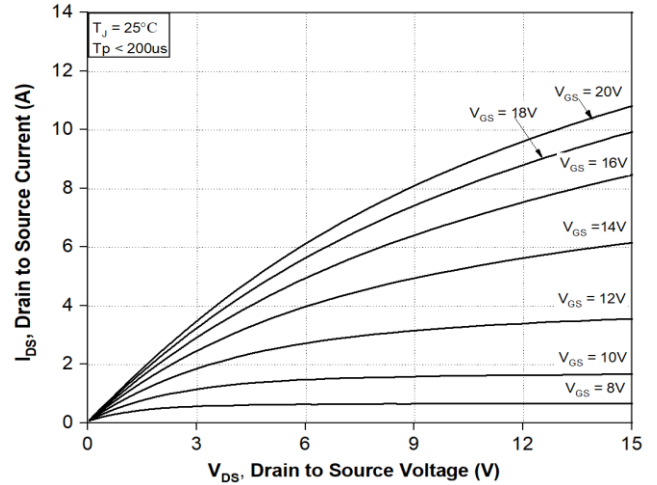


Figure 2. Output Characteristics $T_J = 25^\circ\text{C}$

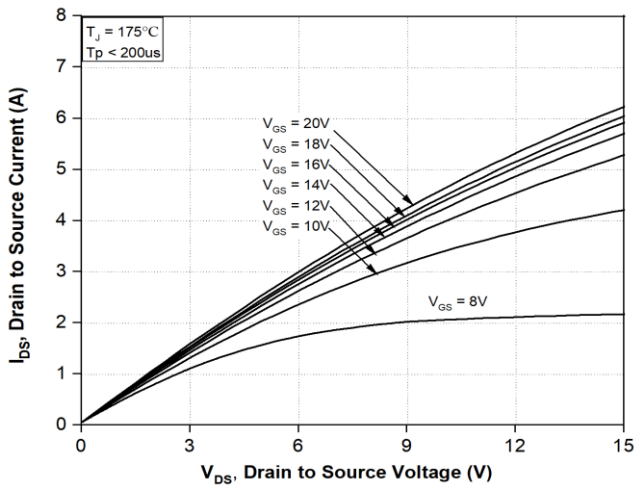


Figure 3. Output Characteristics $T_J = 175^\circ\text{C}$

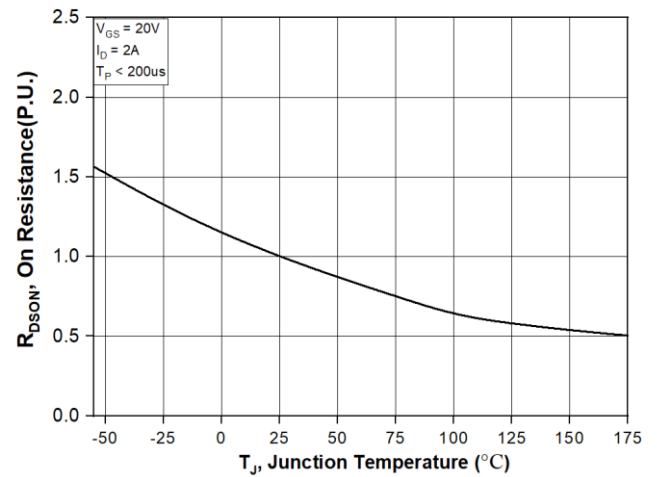


Figure 4. Normalized On-Resistance vs. Temperature

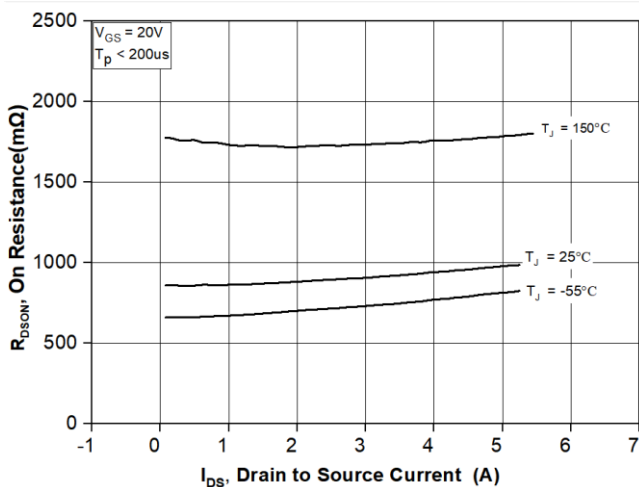


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

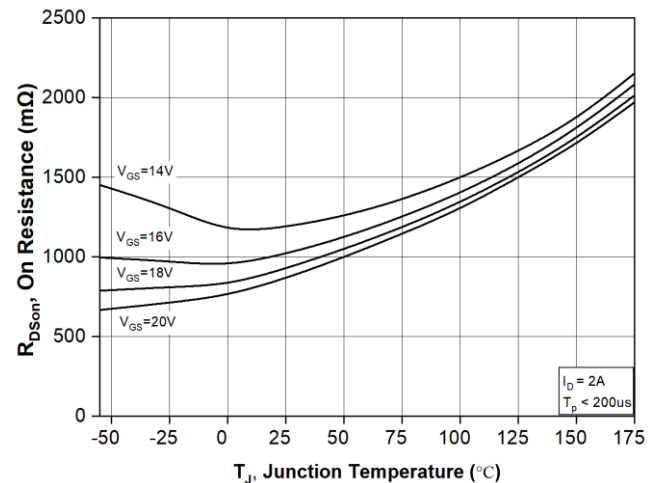


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

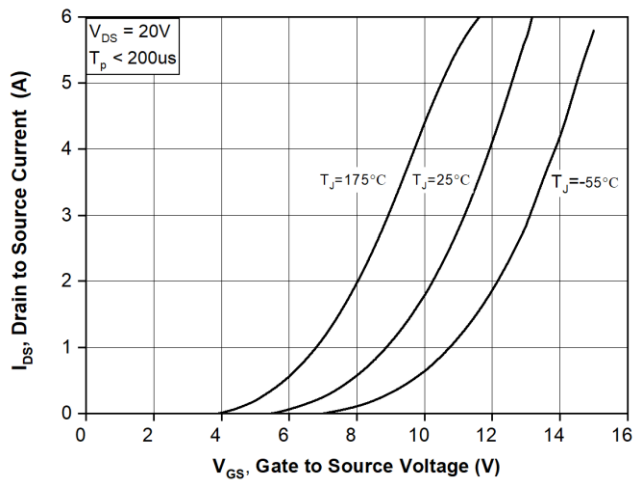


Figure 7. Transfer Characteristic for Various Junction Temperatures

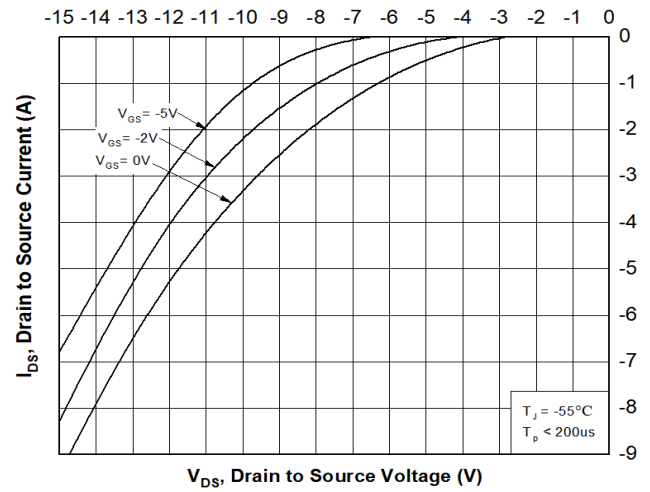


Figure 8. Body Diode Characteristic at $T_J = -55^\circ\text{C}$

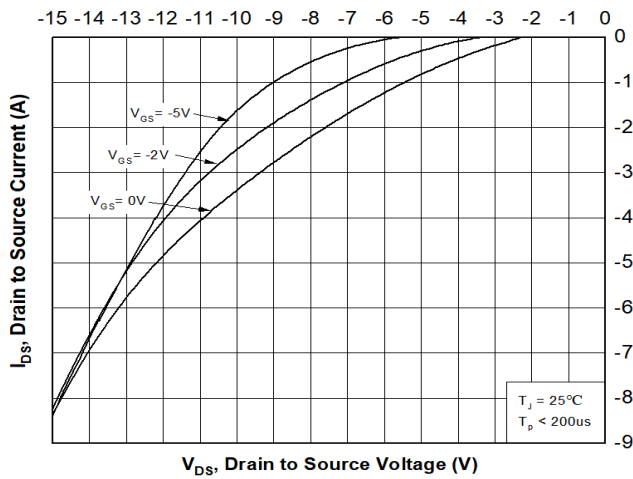


Figure 9. Body Diode Characteristic at $T_J = 25^\circ\text{C}$

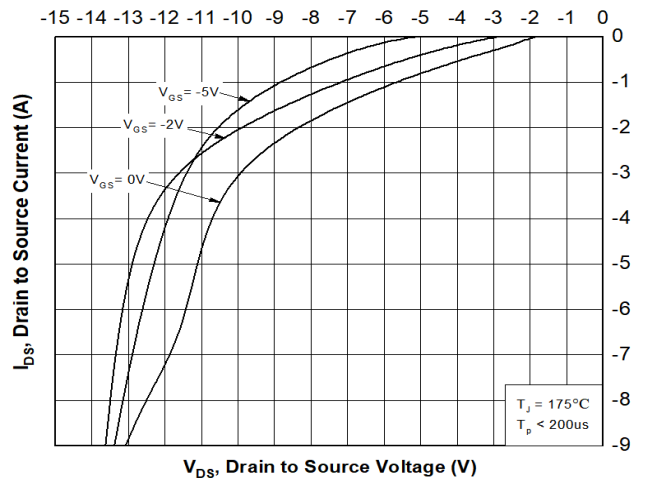


Figure 10. Body Diode Characteristic at $T_J = 175^\circ\text{C}$

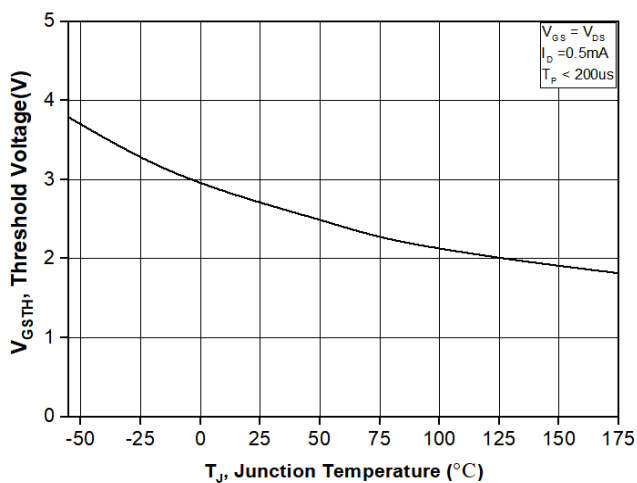


Figure 11. Threshold Voltage vs. Temperature

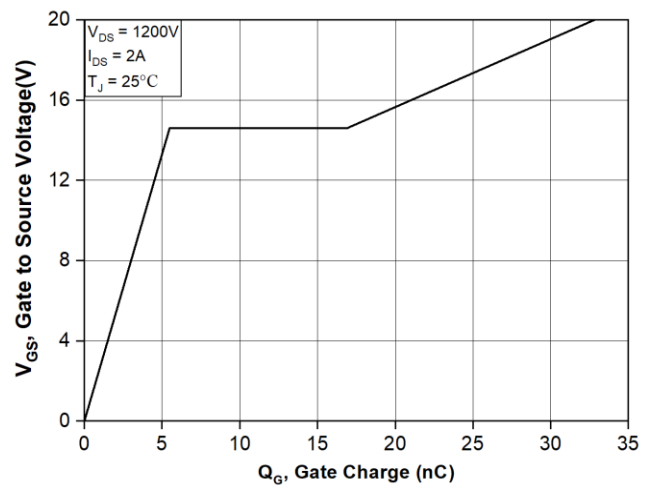


Figure 12. Gate Charge Characteristic

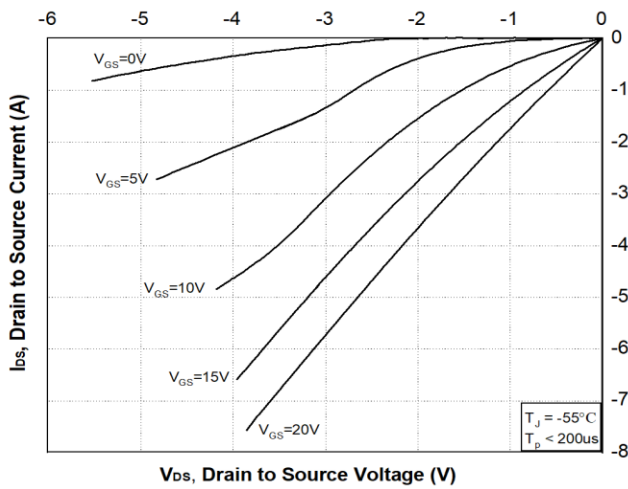


Figure 13. 3rd Quadrant Characteristic at $T_J = -55^\circ\text{C}$

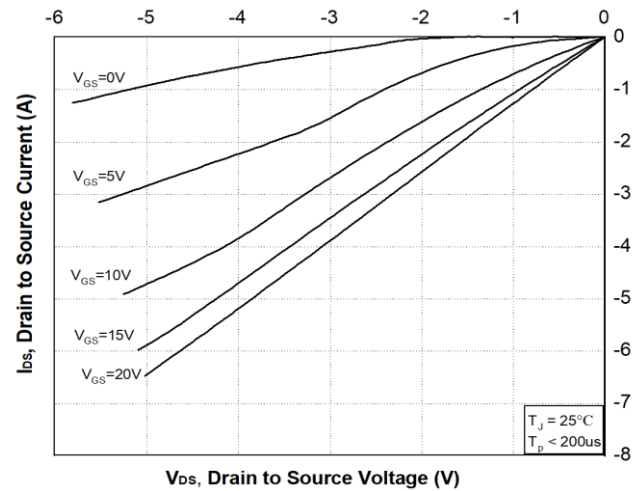


Figure 14. 3rd Quadrant Characteristic at $T_J = 25^\circ\text{C}$

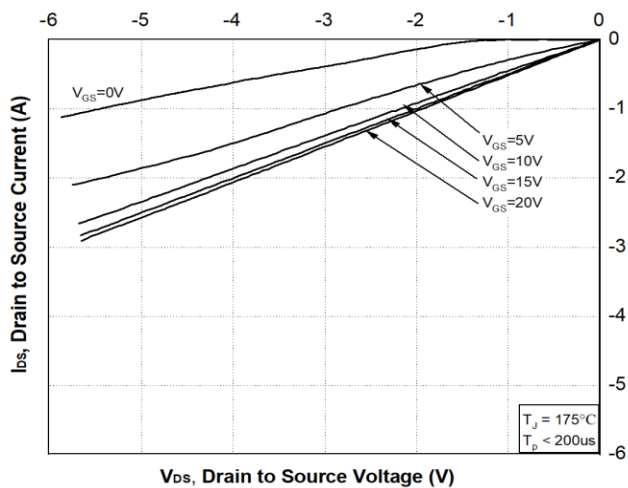


Figure 15. 3rd Quadrant Characteristic at $T_J = 175^\circ\text{C}$

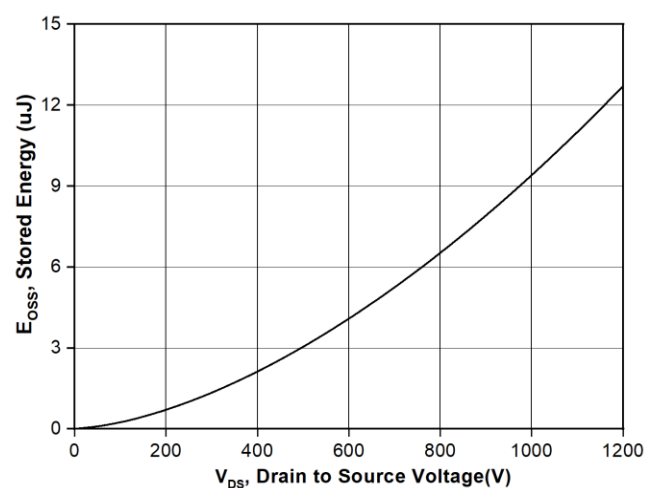


Figure 16. Output Capacitor Stored Energy

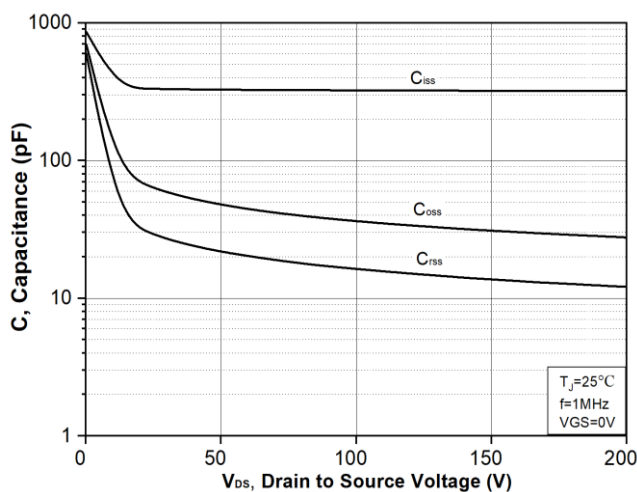


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

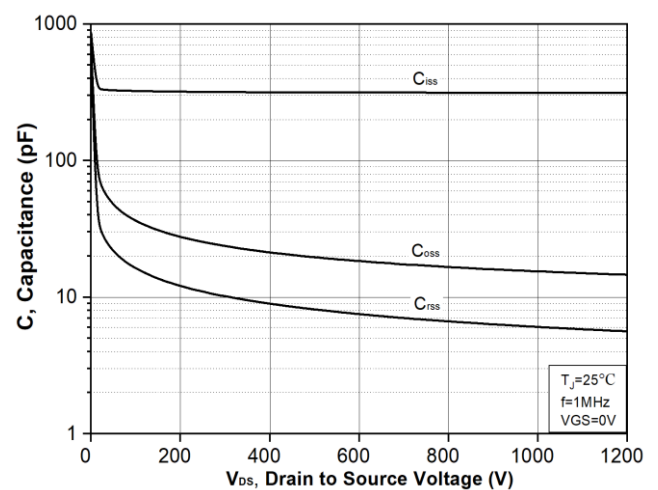


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200V)

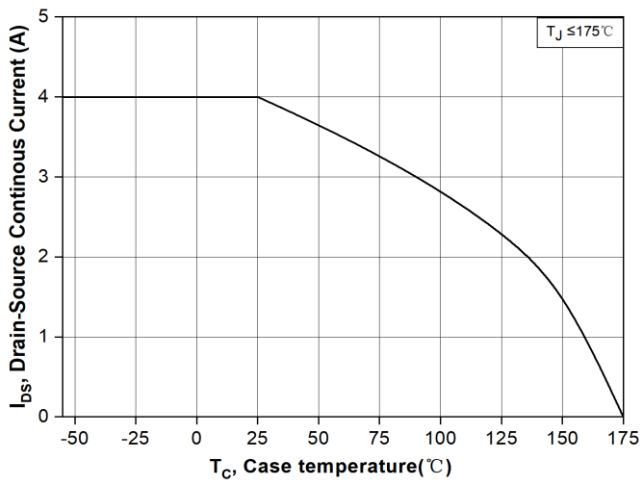


Figure 19. Continuous Drain Current Derating vs. Case Temperature

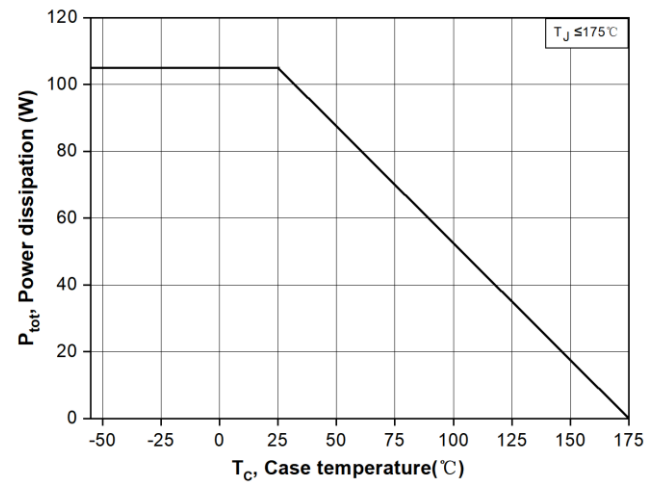


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

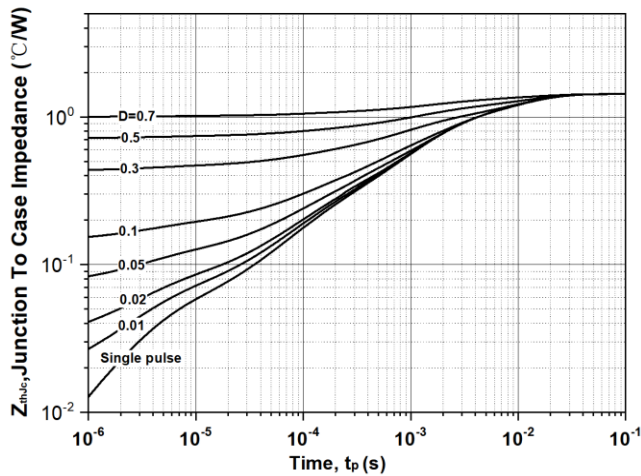


Figure 21. Transient Thermal Impedance (Junction - Case)

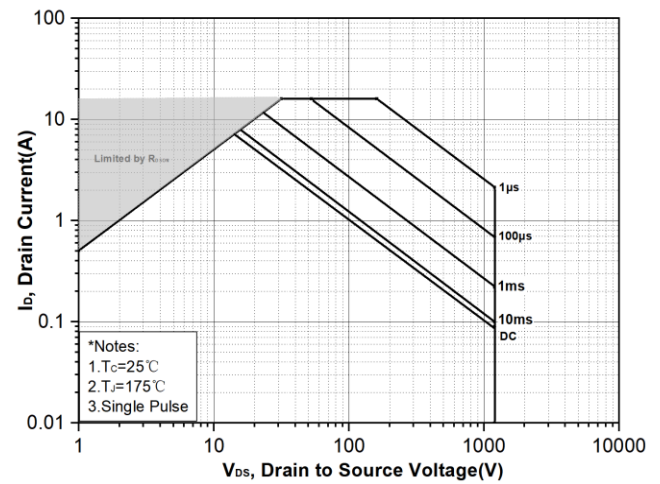


Figure 22. Safe Operating Area

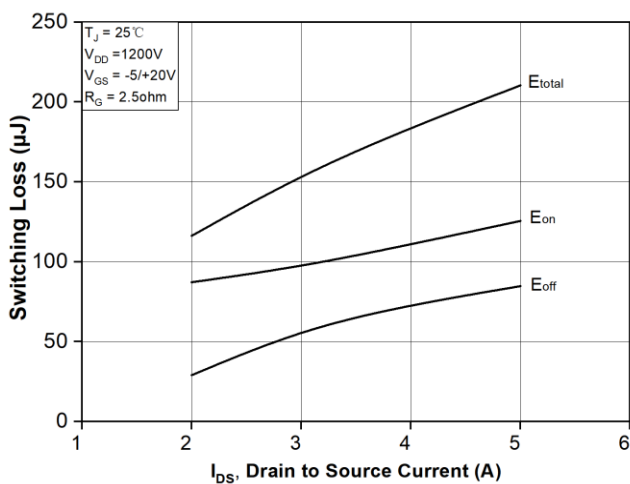


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 1200V$)

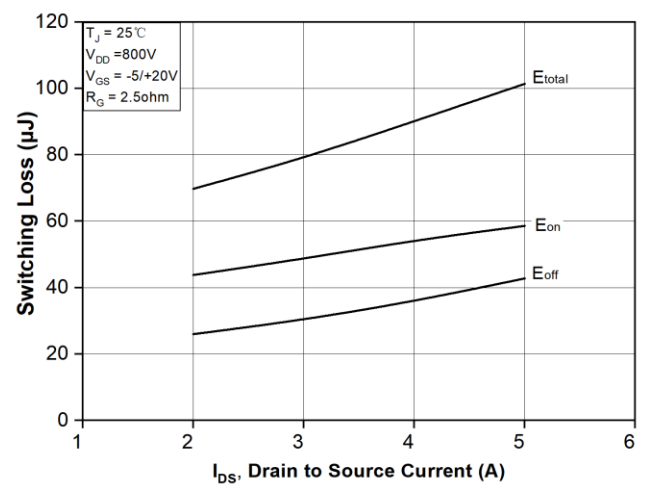


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 800V$)

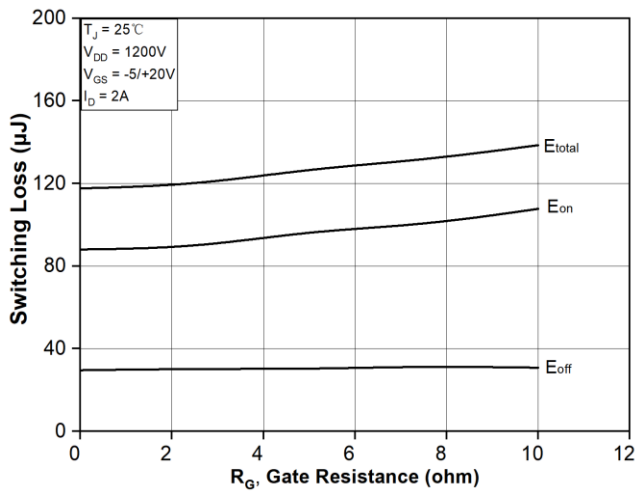


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

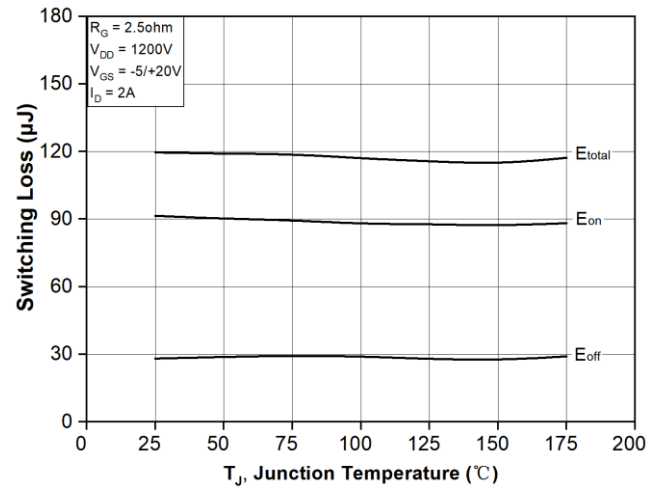


Figure 26. Clamped Inductive Switching Energy vs. Temperature

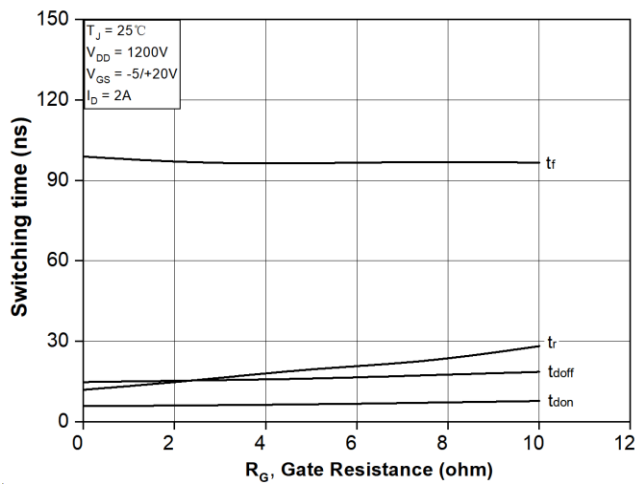


Figure 27. Switching Times vs. $R_{G(ext)}$

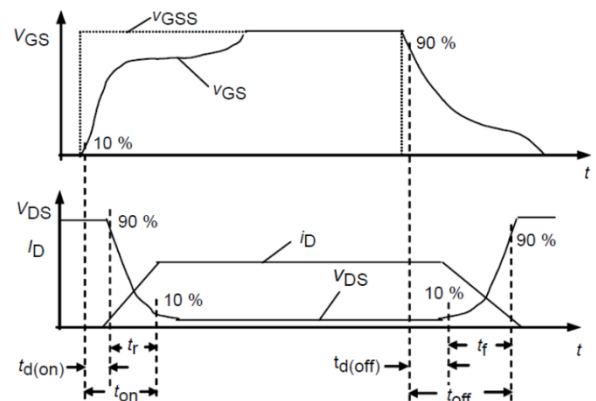
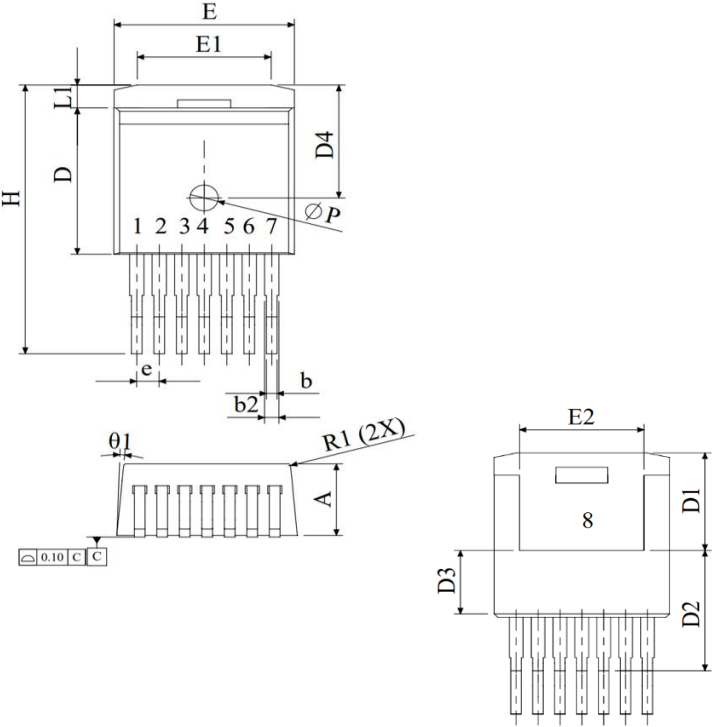


Figure 28. Switching Times Definition

Package Outline (Unit:mm)

TO-263-7L



SYMBOL	MIN (mm)	MAX (mm)
A	4.30	4.57
A1	0.00	0.25
b	0.50	0.70
b2	0.60	1.00
c	0.33	0.65
C2	1.17	1.40
D	9.025	9.125
D1	4.70	4.90
D2	7.170 REF	
D3	4.000 REF	
D4	7.000 REF	
A2	2.595 REF	
E	10.13	10.23
E1	6.50	8.60
E2	6.778	7.665
e	1.27 TYP	
H	15.043	17.313
L	2.324	2.700
L1	0.968	1.868
R	0.506 REF	
R1	0.500 REF	
θ	0°	8°
θ1	4.5°	5.5°
θ2	4°	6°
θ3	4°	6°

***Important Usage Information and Disclaimer**

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